T0295J-1xxT

10-Gb/s CWDM (1470 nm to 1610 nm) DFB TO-Can



Product Brief



Description

Broadcom's TO295J-1xxT CWDM is a hermetically sealed device with a photo diode for optical output monitoring. It incorporates 1470 nm ~ 1610 nm single-mode, edge-emitting laser diode chips for use in uncooled applications up to 10.7 Gb/s. The laser is mounted into a TO header and is hermetically sealed with a specific lens cap. The laser design is a buried hetero structure with multi-quantum well (MQW) active layers and distributed-feedback (DFB) grating layer. All laser chips come from wafers that have been certified using a representative lot of devices that must achieve an acceptable yield for burn-in and other multi-temperature, CW, and dynamic tests.

Features

- Low threshold current
- High bandwidth
- Qualified per intent of Telcordia GR-468
- Operating temperature –5°C to 75°C

Applications

- Supports performance up to 10.7-Gb/s bit rate
- LR1 SONET/SDH OC192/STM-64

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